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Team Nexperia

NPN resistor-equipped transistors; R1 = 22 k Ω , R2 = 47 k Ω

Rev. 07 — 16 November 2009

Product data sheet

1. Product profile

1.1 General description

NPN Resistor-Equipped Transistors (RET) family.

Table 1. Product overview

Type number	Package	Package			
	NXP	JEITA	JEDEC		
PDTC124XE	SOT416	SC-75	-	PDTA124XE	
PDTC124XEF	SOT490	SC-89	-	PDTA124XEF	
PDTC124XK	SOT346	SC-59A	TO-236	PDTA124XK	
PDTC124XM	SOT883	SC-101	-	PDTA124XM	
PDTC124XS ^[1]	SOT54	SC-43A	TO-92	PDTA124XS	
PDTC124XT	SOT23	-	TO-236AB	PDTA124XT	
PDTC124XU	SOT323	SC-70	-	PDTA124XU	

[1] Also available in SOT54A and SOT54 variant packages (see Section 2).

1.2 Features

- Built-in bias resistors
- Simplifies circuit design

1.3 Applications

- General-purpose switching and amplification
- Inverter and interface circuits

1.4 Quick reference data

Table 2.Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	50	V
lo	output current		-	-	100	mA
R1	bias resistor 1 (input)		15.4	22	28.6	kΩ
R2/R1	bias resistor ratio		1.7	2.1	2.6	



- Reduces component count
- Reduces pick and place costs
- Circuit drivers

2. Pinning information

Pin	Description	Simplified outline	Symbol
SOT54			
1	input (base)		
2	output (collector)		
3	GND (emitter)		
		001aab347	006aaa145
SOT54A			
1	input (base)		
2	output (collector)		
3	GND (emitter)		
		001aab348	
			006aaa145
SOT54 va	riant		
1	input (base)		
2	output (collector)		
3	GND (emitter)		
		001aab447	
			006aaa145
SOT23; So	OT323; SOT346; SOT416; SOT490		
1	input (base)	_	
2	GND (emitter)	3	
3	output (collector)		
			R2
		1 2	
		006aaa144	sym007
SOT883			
1	input (base)		
2	GND (emitter)		
3	output (collector)	2	
		Transparent top view	R2

3. Ordering information

Type number	Package		
	Name	Description	Version
PDTC124XE	SC-75	plastic surface mounted package; 3 leads	SOT416
PDTC124XEF	SC-89	plastic surface mounted package; 3 leads	SOT490
PDTC124XK	SC-59A	plastic surface mounted package; 3 leads	SOT346
PDTC124XM	SC-101	leadless ultra small plastic package; 3 solder lands; body 1.0 \times 0.6 \times 0.5 mm	SOT883
PDTC124XS ^[1]	SC-43A	plastic single-ended leaded (through hole) package; 3 leads	SOT54
PDTC124XT	-	plastic surface mounted package; 3 leads	SOT23
PDTC124XU	SC-70	plastic surface mounted package; 3 leads	SOT323

[1] Also available in SOT54A and SOT54 variant packages (see Section 2 and Section 9).

4. Marking

Table 5. Marking codes	
Type number	Marking code ^[1]
PDTC124XE	32
PDTC124XEF	32
PDTC124XK	51
PDTC124XM	DZ
PDTC124XS	TC124X
PDTC124XT	*46
PDTC124XU	*51

[1] * = -: made in Hong Kong

* = p: made in Hong Kong

* = t: made in Malaysia

* = W: made in China

5. Limiting values

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter	-	50	V
V _{CEO}	collector-emitter voltage	open base	-	50	V
V _{EBO}	emitter-base voltage	open collector	-	7	V
VI	input voltage				
	positive		-	+40	V
	negative		-	-7	V
I _O	output current		-	100	mA
I _{CM}	peak collector current	single pulse; $t_p \leq 1 \text{ ms}$	-	100	mA
P _{tot}	total power dissipation	$T_{amb} \leq 25 ~^{\circ}C$			
	SOT416		<u>[1]</u> _	150	mW
	SOT490		<u>[1][2]</u>	250	mW
	SOT346		<u>[1]</u> _	250	mW
	SOT883		[2][3]	250	mW
	SOT54		<u>[1]</u> _	500	mW
	SOT23		<u>[1]</u> _	250	mW
	SOT323		<u>[1]</u> _	200	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

[3] Device mounted on an FR4 PCB with 60 µm copper strip line, standard footprint.

6. Thermal characteristics

Table 7.	Thermal characteristics	5				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air				
	SOT416		<u>[1]</u> -	-	833	K/W
	SOT490		<u>[1][2]</u> _	-	500	K/W
	SOT346		<u>[1]</u> _	-	500	K/W
	SOT883		[2][3] _	-	500	K/W
	SOT54		<u>[1]</u> _	-	250	K/W
	SOT23		<u>[1]</u> -	-	500	K/W
	SOT323		<u>[1]</u> -	-	625	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

[3] Device mounted on an FR4 PCB with 60 µm copper strip line, standard footprint.

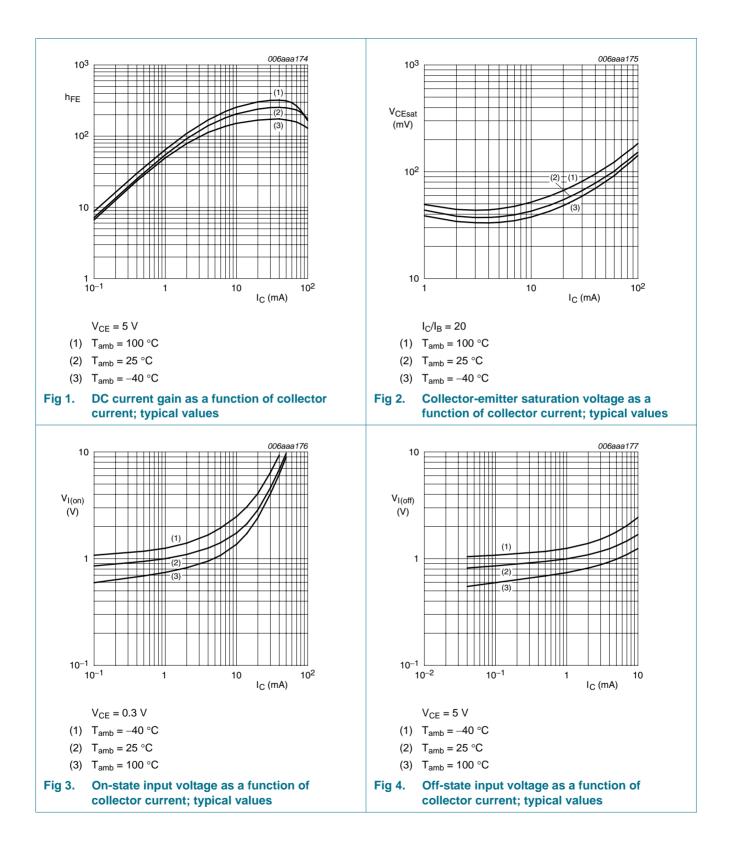
7. Characteristics

Table 8. Characteristics

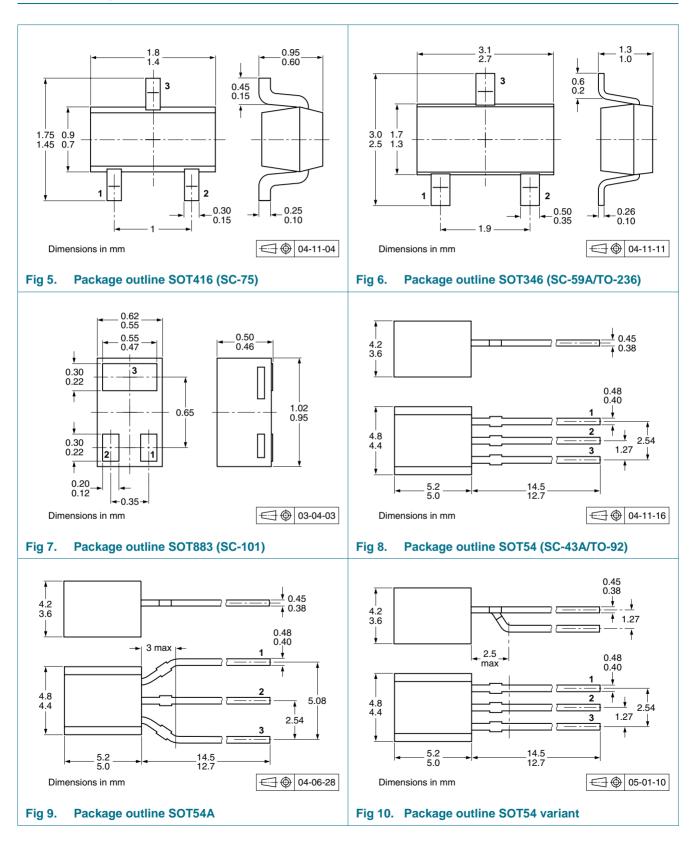
 $T_{amb} = 25 \$ °C unless otherwise specified.

Parameter	Conditions	Min	Тур	Max	Unit
collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nA
collector-emitter	$V_{CE} = 30 \text{ V}; I_B = 0 \text{ A}$	-	-	1	μA
cut-off current	$\label{eq:VCE} \begin{array}{l} V_{CE} = 30 \; V; \; I_{B} = 0 \; A; \\ T_{j} = 150 \; ^{\circ}C \end{array}$	-	-	50	μA
emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}$	-	-	120	μΑ
DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 5 \text{ mA}$	80	-	-	
collector-emitter saturation voltage	I _C = 10 mA; I _B = 0.5 mA	-	-	150	mV
off-state input voltage	V_{CE} = 5 V; I_C = 100 μ A	-	0.8	0.5	V
on-state input voltage	V_{CE} = 300 mV; I_C = 2 mA	2	1.1	-	V
bias resistor 1 (input)		15.4	22	28.6	kΩ
bias resistor ratio		1.7	2.1	2.6	
collector capacitance	V_{CB} = 10 V; I_E = i_e = 0 A; f = 1 MHz	-	-	2.5	pF
	collector-base cut-off current collector-emitter cut-off current emitter-base cut-off current DC current gain Collector-emitter saturation voltage off-state input voltage on-state input voltage bias resistor 1 (input) bias resistor ratio	collector-base cut-off current $V_{CB} = 50 \text{ V}; \text{ I}_E = 0 \text{ A}$ collector-emitter cut-off current $V_{CE} = 30 \text{ V}; \text{ I}_B = 0 \text{ A}$ $V_{CE} = 30 \text{ V}; \text{ I}_B = 0 \text{ A};$ $T_j = 150 °C$ $V_{CE} = 30 \text{ V}; \text{ I}_B = 0 \text{ A};$ emitter-base cut-off current $V_{EB} = 5 \text{ V}; \text{ I}_C = 0 \text{ A}$ DC current gain $V_{CE} = 5 \text{ V}; \text{ I}_C = 5 \text{ mA}$ collector-emitter saturation voltage $I_C = 10 \text{ mA}; \text{ I}_B = 0.5 \text{ mA}$ off-state input voltage $V_{CE} = 5 \text{ V}; \text{ I}_C = 100 \mu \text{ A}$ on-state input voltage $V_{CE} = 300 \text{ mV}; \text{ I}_C = 2 \text{ mA}$ bias resistor 1 (input)bias resistor ratiocollector capacitance $V_{CB} = 10 \text{ V}; \text{ I}_E = i_e = 0 \text{ A};$		collector-base cut-off current $V_{CB} = 50 \text{ V}; \text{ I}_E = 0 \text{ A}$ - - collector-emitter cut-off current $V_{CE} = 30 \text{ V}; \text{ I}_B = 0 \text{ A};$ - - $V_{CE} = 30 \text{ V}; \text{ I}_B = 0 \text{ A};$ - - - $V_{CE} = 30 \text{ V}; \text{ I}_B = 0 \text{ A};$ - - - $V_{CE} = 30 \text{ V}; \text{ I}_B = 0 \text{ A};$ - - - emitter-base cut-off current $V_{EB} = 5 \text{ V}; \text{ I}_C = 0 \text{ A}$ - - DC current gain $V_{CE} = 5 \text{ V}; \text{ I}_C = 5 \text{ MA}$ 80 - collector-emitter saturation voltage $I_C = 10 \text{ mA}; \text{ I}_B = 0.5 \text{ mA}$ - - off-state input voltage $V_{CE} = 5 \text{ V}; \text{ I}_C = 100 \ \mu\text{A}$ - 0.8 on-state input voltage $V_{CE} = 300 \text{ mV}; \text{ I}_C = 2 \text{ mA}$ 2 1.1 bias resistor 1 (input) 15.4 22 bias resistor ratio $V_{CB} = 10 \text{ V}; \text{ I}_E = i_e = 0 \text{ A};$ - -	collector-base cut-off current $V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$ - - 100 collector-emitter cut-off current $V_{CE} = 30 \text{ V}; I_B = 0 \text{ A};$ - - 1 $V_{CE} = 30 \text{ V}; I_B = 0 \text{ A};$ - - - 1 $V_{CE} = 30 \text{ V}; I_B = 0 \text{ A};$ - - 50 emitter-base cut-off current $V_{EB} = 5 \text{ V}; I_C = 0 \text{ A}$ - - 120 DC current gain $V_{CE} = 5 \text{ V}; I_C = 5 \text{ MA}$ 80 - - collector-emitter saturation voltage $I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$ - - 150 off-state input voltage $V_{CE} = 5 \text{ V}; I_C = 100 \ \mu\text{A}$ - 0.8 0.5 on-state input voltage $V_{CE} = 300 \text{ mV}; I_C = 2 \text{ mA}$ 2 1.1 - bias resistor 1 (input) V_{CE} = 300 \text{ mV}; I_C = 2 \text{ mA} 2.1 2.6 bias resistor ratio $V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ - 2.5

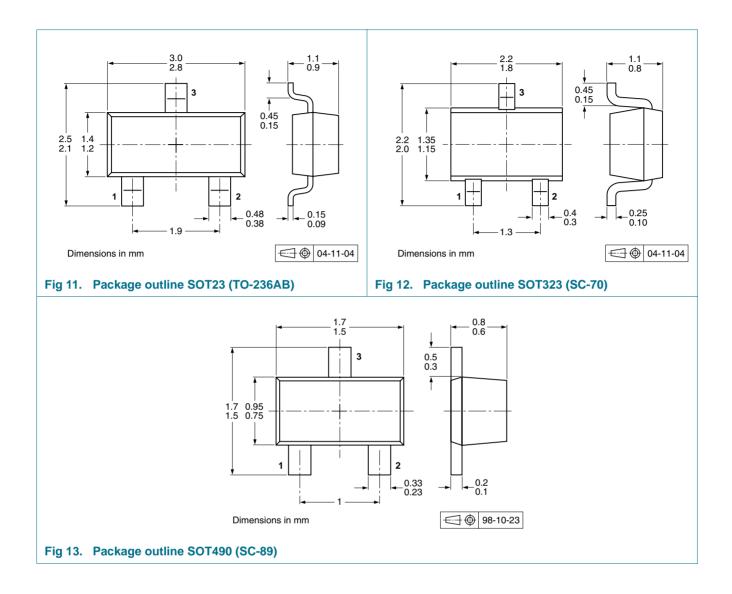
NPN resistor-equipped transistors; R1 = 22 k Ω , R2 = 47 k Ω



8. Package outline



NPN resistor-equipped transistors; R1 = 22 k Ω , R2 = 47 k Ω



9. Packing information

Type number	Package	Description	Packi	ng qua	ntity	
				4000	5000	10000
PDTC124XE	SOT416	4 mm pitch, 8 mm tape and reel	-115	-	-	-135
PDTC124XEF	SOT490	4 mm pitch, 8 mm tape and reel	-	-115	-	-
PDTC124XK	SOT346	4 mm pitch, 8 mm tape and reel	-115	-	-	-135
PDTC124XM	SOT883	2 mm pitch, 8 mm tape and reel	-	-	-	-315
PDTC124XS SOT54 SOT54A	SOT54	bulk, straight leads	-	-	-412	-
	SOT54A	tape and reel, wide pitch	-	-	-	-116
		tape ammopack, wide pitch	-	-	-	-126
	SOT54 variant	bulk, delta pinning	-	-	-112	-
PDTC124XT	SOT23	4 mm pitch, 8 mm tape and reel	-215	-	-	-235
PDTC124XU	SOT323	4 mm pitch, 8 mm tape and reel	-115	-	-	-135

[1] For further information and the availability of packing methods, see <u>Section 12</u>.

10. Revision history

Table 10. Revision hist	tory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PDTC124X_SER_7	20091116	Product data sheet	-	PDTC124X_SER_6
Modifications:		eet was changed to reflect the v legal definitions and disclair		
PDTC124X_SER_6	20050714	Product data sheet	-	PDTC124X_SERIES_5
PDTC124X_SERIES_5	20040813	Product specification	-	PDTC124X_SERIES_4
PDTC124X_SERIES_4	20030410	Product specification	-	PDTC124XEF_2 PDTC124XE_3
PDTC124XE_3	19990518	Product specification	-	PDTC124XE_2
PDTC124XE_2	19980921	Product specification	-	PDTC124XE_1
PDTC124XE_1	19971215	Product specification	-	-
PDTC124XEF_2	19990518	Preliminary specification	-	PDTC124XEF_1
PDTC124XEF_1	19981111	Preliminary specification	-	-

11. Legal information

11.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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NPN resistor-equipped transistors; $\overline{R1} = 22 \text{ k}\Omega$, $R2 = 47 \text{ k}\Omega$

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